

1N914 THRU 1N4454

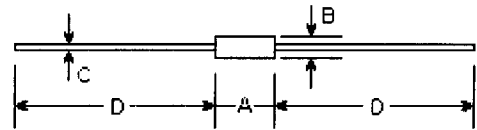
SILICON EPITAXIAL PLANAR DIODES

Features

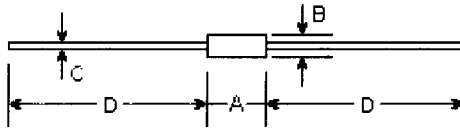
Silicon Epitaxial Planar Diodes
for general purpose and switching

The types 1N4149, 1N4447 and 1N4449 are also available
in glass case DO-34.

DO-35



DO-34



| DIM | inches | | mm | | Note |
|-----|--------|-------|------|------|------|
| | Min. | Max. | Min. | Max. | |
| A | - | 0.114 | - | 2.9 | |
| B | - | 0.075 | - | 1.9 | φ |
| C | - | 0.017 | - | 0.42 | φ |
| D | 0.930 | - | 23.8 | - | |

| DIM | inches | | mm | | Note |
|-----|--------|-------|-------|------|------|
| | Min. | Max. | Min. | Max. | |
| A | - | 0.154 | - | 3.9 | |
| B | - | 0.075 | - | 1.9 | φ |
| C | - | 0.020 | - | 0.52 | φ |
| D | 1.083 | - | 27.50 | - | |

Electrical Characteristics

| Type | Peak reverse voltage | Max. aver. rectified current | Max. power dissip. at 25°C | Max. junction temperature | Max. forward voltage drop | | Max. reverse current | | Max. reverse recovery time | |
|-----------------------|----------------------|------------------------------|----------------------------|---------------------------|---------------------------|-------------|----------------------|------------|----------------------------|--|
| | V_{RM} V | I_O mA | P_{tot} mW | T_J °C | V_F V | at I_F mA | I_R nA | at V_R V | t_r nS | Conditions |
| 1N914 | 100 | 75 | 500 | 200 | 1.0 | 10 | 25 | 20 | Max. 4.0 | $I_F=10$ mA, $V_R=6$ V, $R_L=100$ Ω, to $I_R=1$ mA |
| 1N4149 ⁽¹⁾ | 100 | 150 | 500 | 200 | 1.0 | 10 | 25 | 20 | Max. 4.0 | $I_F=10$ mA, $V_R=6$ V, $R_L=100$ Ω, to $I_R=1$ mA |
| 1N4150 | 50 | 200 | 500 | 200 | 1.0 | 200 | 100 | 50 | Max. 4.0 | $I_F=I_R=10$ to 200 mA, to 0.1 I_F |
| 1N4152 | 40 | 150 | 400 | 175 | 0.55 | 0.10 | 50 | 30 | Max. 2.0 | $I_F=10$ mA, $V_R=6$ V, $R_L=100$ Ω, to $I_R=1$ mA |
| 1N4153 | 75 | 150 | 400 | 175 | 0.55 | 0.10 | 50 | 50 | Max. 2.0 | $I_F=10$ mA, $V_R=6$ V, $R_L=100$ Ω, to $I_R=1$ mA |
| 1N4154 | 35 | 150 ⁽²⁾ | 500 | 200 | 1.0 | 0.10 | 100 | 25 | Max. 2.0 | $I_F=10$ mA, $V_R=6$ V, $R_L=100$ Ω, to $I_R=1$ mA |
| 1N4447 ⁽¹⁾ | 100 | 150 | 500 | 200 | 1.0 | 20 | 25 | 20 | Max. 4.0 | $I_F=10$ mA, $V_R=6$ V, $R_L=100$ Ω, to $I_R=1$ mA |
| 1N4449 ⁽¹⁾ | 100 | 150 | 500 | 200 | 1.0 | 30 | 25 | 20 | Max. 4.0 | $I_F=10$ mA, $V_R=6$ V, $R_L=100$ Ω, to $I_R=1$ mA |
| 1N4450 | 40 | 150 | 400 | 175 | 0.54 | 0.50 | 50 | 30 | Max. 4.0 | $I_F=I_R=10$ mA, to $I_R=1$ mA |
| 1N4451 | 40 | 150 | 400 | 175 | 0.50 | 0.10 | 50 | 30 | Max. 10 | $I_F=I_R=10$ mA, to $I_R=1$ mA |
| 1N4453 | 30 | 150 | 400 | 175 | 0.55 | 0.01 | 50 | 20 | - | - |
| 1N4454 | 75 | 150 | 400 | 175 | 1.0 | 10 | 100 | 50 | Max. 4.0 | $I_F=I_R=10$ mA, to $I_R=1$ mA |

Notes:

- These diodes are also available in glass case DO-34
- Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature
Parameters for diodes in case DO-34: $P_{tot}=300$ mW $T_J=-65$ to $+175$ °C
 $T_J=175$ °C $R_{th} \leq 0.4$ K/mW



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